



# DATA SHEET

SEMICONDUCTOR

**U2A Thru U2M**

**SURFACE MOUNT REVERSE VOLTAGE - 50 to 1000 Volts  
ULTRA FAST RECTIFIERS FORWARD CURRENT - 2 Ampere**



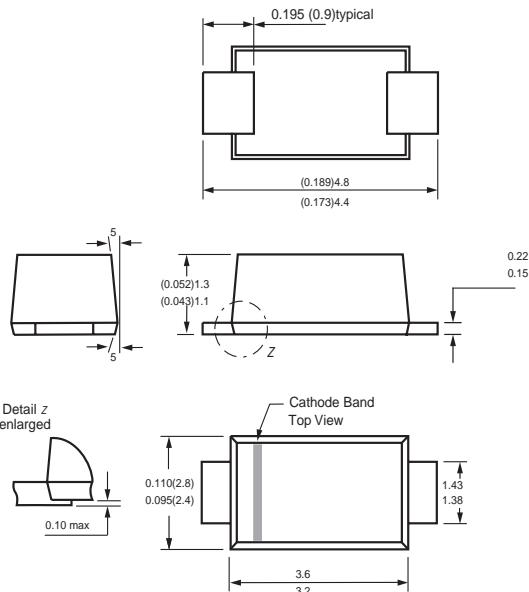
SMF Unit: inch ( mm )

## FEATURES

- Glass passivated chip
- Ultra fast switching for high efficiency
- For surface mounted applications
- Low forward voltage drop and high current capability
- Low reverse leakage current
- Plastic material has UL flammability classification 94V-0
- High temperature soldering : 260°C / 10 seconds at terminals
- Pb free product available : 99% Sn above meet RoHS environment substance directive request

## MECHANICAL DATA

- Case: ITO-220AB full molded plastic package
- Case : Molded plastic
- Polarity : Indicated by cathode band
- Weight : 0.002 ounces, 0.064 grams



## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

CHARACTERISTICS	SYMBOL	U2A	U2B	U2D	U2G	U2J	U2K	U2M	UNITS
<b>Maximum Recurrent Peak Reverse Voltage</b>	VR <sub>RM</sub>	50	100	200	400	600	800	1000	V
<b>Maximum RMS Voltage</b>	VR <sub>MS</sub>	35	70	140	280	420	560	700	V
<b>Maximum DC Blocking Voltage</b>	V <sub>DC</sub>	50	100	200	400	600	800	1000	V
<b>Maximum Average Forward Rectified Current @T<sub>L</sub> =75°C</b>	IA <sub>V</sub>					2.0			A
<b>Peak Forward Surge Current 8.3ms single half sine-wave super imposed on rated load (JEDEC METHOD)</b>	I <sub>FSM</sub>				60				A
<b>Maximum forward Voltage at 1.0A DC</b>	V <sub>F</sub>		1.0		1.3	1.5	1.7		V
<b>Maximum DC Reverse Current @T<sub>J</sub> =25°C at Rated DC Blocking Voltage @T<sub>J</sub> =100°C</b>	I <sub>R</sub>				5	100			µA
<b>Maximum Reverse Recovery Time (Note 1)</b>	C <sub>J</sub>		20			10			pF
<b>Typical Junction Capacitance (Note 2)</b>	T <sub>RR</sub>		50			75			ns
<b>Typical Thermal Resistance (Note 3)</b>	R <sub>OJC</sub>		30						°C/W
<b>Operating Temperature Range</b>	T <sub>J</sub>		-55 to +150						°C
<b>Storage Temperature Range</b>	T <sub>STG</sub>		-55 to +150						°C

### NOTES:

1. Measured at 1 MHz and applied reverse voltage of 4.0 VDC.
2. Reverse Recovery Test Conditions: I<sub>F</sub>=.5A, I<sub>R</sub>=1A, I<sub>rr</sub>=.25A.
3. Thermal resistance from Junction to ambient and from junction to lead 0.375" (9.5mm) P.C.B mounted.

# RATING AND CHARACTERISTIC CURVES

## U2A Thru U2M

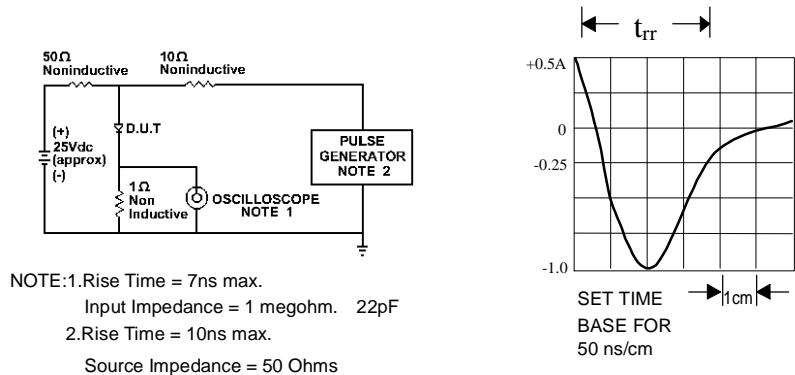


Fig. 1-REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM

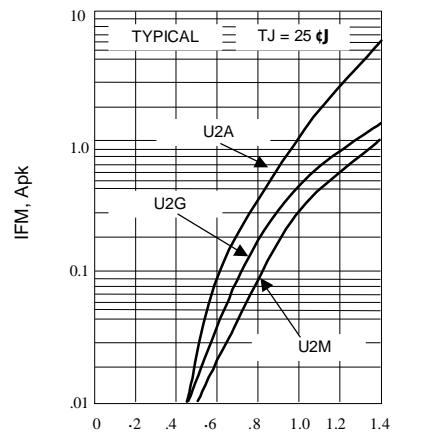


Fig. 2-FORWARD CHARACTERISTICS

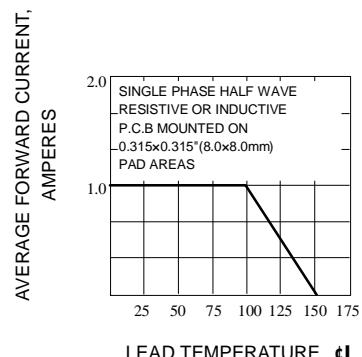


Fig. 3-FORWARD CURRENT DERATING CURVE

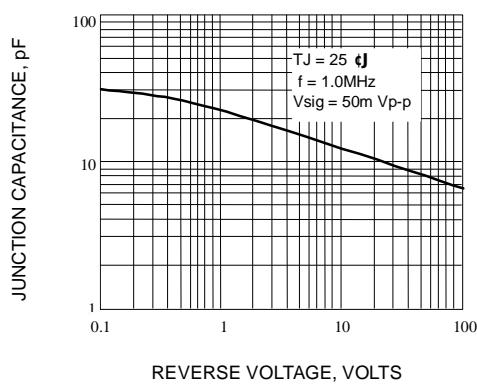


Fig. 4-TYPICAL JUNCTION CAPACITANCE

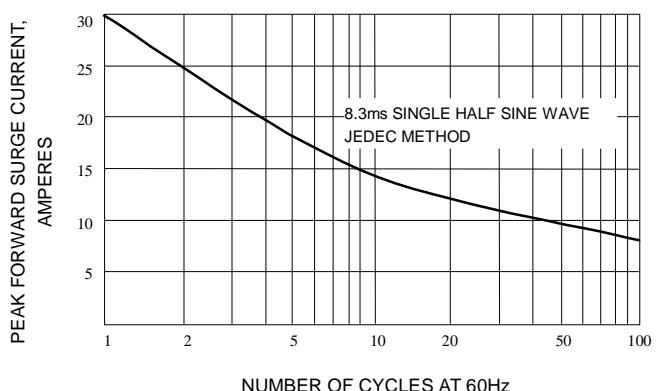


Fig. 5-PEAK FORWARD SURGE CURRENT